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	U	I	Inventor	Document	Issued	P	Title	Current	Current X	Retrieved	S	C	P	S	T	Image	Doc P
1			Mouli, Chan	US 200400	2004	13	SOI device having increased reliability	438/29	257/E21.21		P	C	F	F			US 20040
2			Lydling, Jose	US 200302	2003	11	DEUTERIUM TREATMENT OF SEMICONDUCTOR	438/30	257/E21.19		P	C	F	F			US 20030
3			Watanabe, U	US 200500	2005	16	Semiconductor device with an insulat	257/41			P	C	F	F			US 20050
4			Hosotani, K	US 200500	2005	9	Magnetic random access memory and	438/9			P	C	F	F			US 20050
5			Kumikiyo, T	US 200201	2002	31	Method of manufacturing semiconductor	438/30	257/E21.19		P	C	F	F			US 200201
6			Kumikiyo, T	US 200200	2002	5	Semiconductor device and SOI substr	257/41	257/E21.19		P	C	F	F			US 20020
7			Lydling, Jose	US 200200	2002	11	Deuterium treatment of semiconducto	438/79	257/410;		P	C	F	F			US 20020
8			Lydling, Jos	US 683330	2004	10	Deuterium treatment of semiconducto	438/30	438/795;		P	C	F	F			US 68333
9			Kumikiyo, T	US 666106	2008	5	Semiconductor device and SOI substr	257/41	257/347;		P	C	F	F			US 666106
10			Kumikiyo, T	US 650072	2002	9	Method of manufacturing semiconduc	438/30	257/E21.19		P	C	F	F			US 650072

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